

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High Overload Surge Capability.
2. High Speed Switching.
3. High Reliability.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Rectifier for high voltage power supply.
2. General purpose high voltage rectifier.
3. Rectification for X-ray generator high voltage power supply.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.10 grams (approx).

SHAPE DISPLAY:

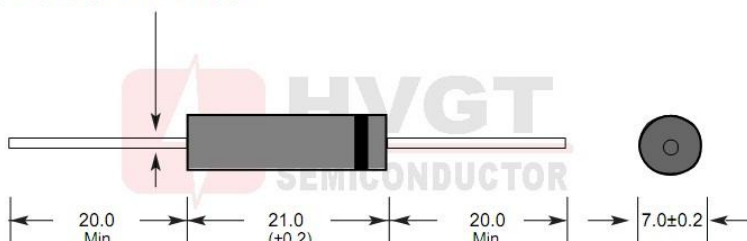


SIZE: (Unit:mm)

HVGT NAME: DO-721

DO-721 Series

Lead Diameter 1.2mm ±0.02



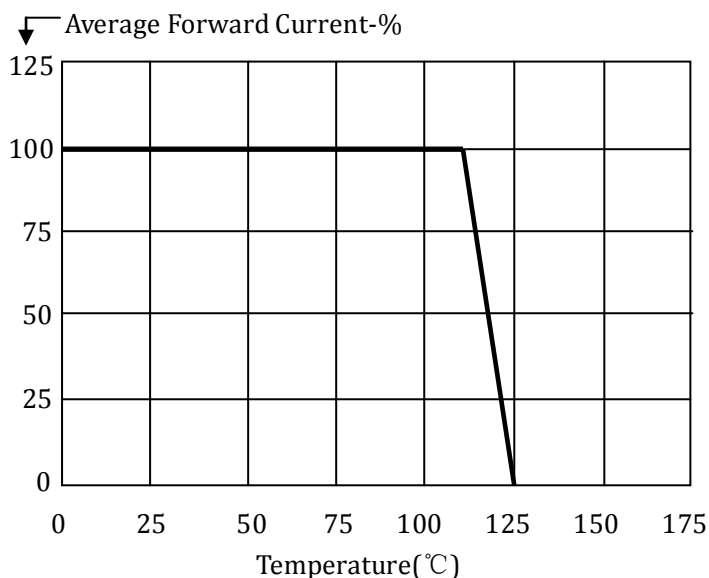
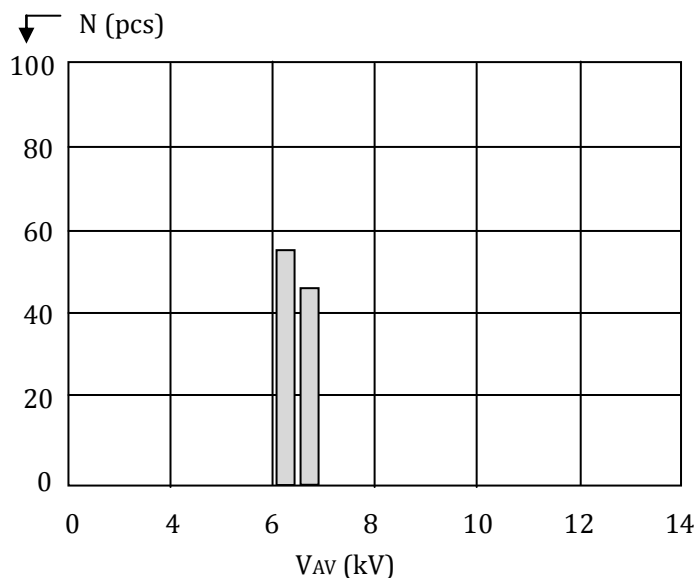
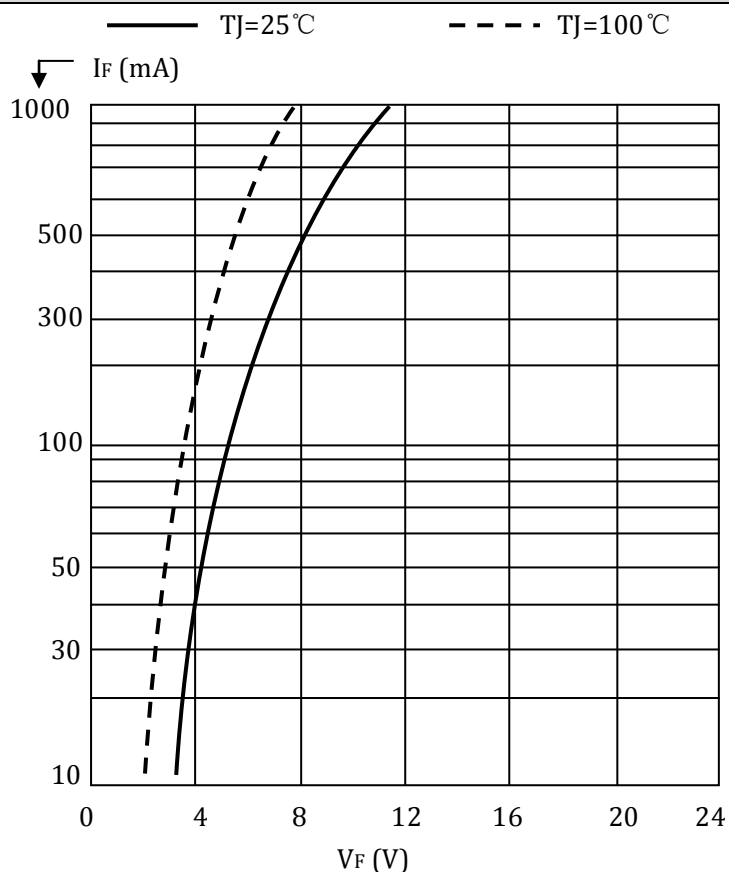
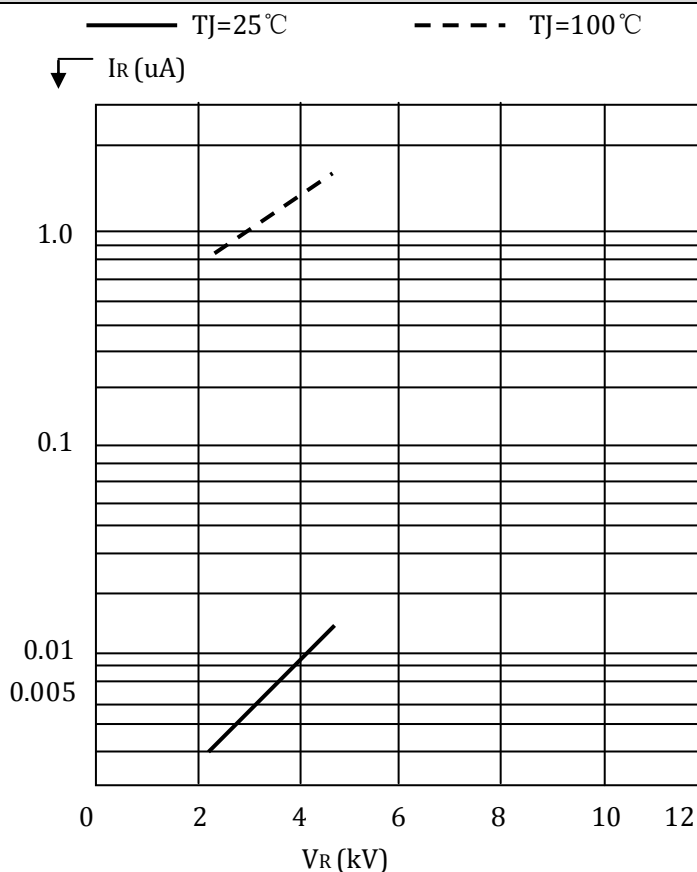
Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	4.5	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$	5.0	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=110^{\circ}C$; Resistive Load	350	mA
		$T_{OIL}=110^{\circ}C$	--	mA
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3ms	15	A
Junction Temperature	T_J		125	$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	12.0	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	10.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	100	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	150	nS
Avalanche Breakdown Voltage	V_{AV}	at $25^{\circ}C$; $I_R=100\mu A$	≥ 5.0	kV

Forward Current Derating Curve

Avalanche Breakdown Voltage
 $T_J=25^{\circ}\text{C}$; $I_R=100\mu\text{A}$; $N=100\text{pcs}$

Forward Characteristics

Reverse Characteristics

Marking
Type
 ESJC30-05

Code
 ESJC30-05
 HVGT

Cathode Mark
